

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

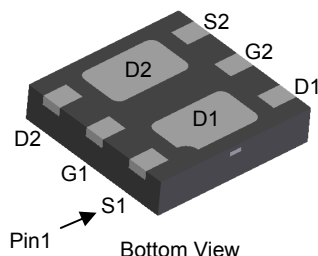
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
20V	45m Ω @ $V_{GS} = 4.5\text{V}$	4.5A
	55m Ω @ $V_{GS} = 2.5\text{V}$	4.1A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

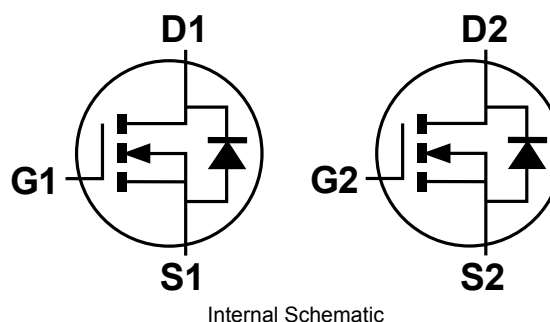


Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: U-DFN2020-6 Type B
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (approximate)

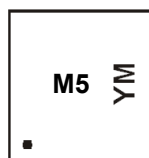


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2050LFDB -7	DFN2020-6 Type B	3,000/Tape & Reel
DMN2050LFDB -13	DFN2020-6 Type B	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



M5 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	3.3	A
		T _A = +70°C		2.6	
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	4.5	A
		T _A = +70°C		3.6	
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	1	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	25	A
Avalanche Current (Note 7) L = 0.1mH			I _{AR}	9	A
Repetitive Avalanche Energy (Note 7) L = 0.1mH			E _{AR}	4.5	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.73	W
	T _A = +70°C		0.46	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	173	°C/W
	t < 10s		110	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.42	W
	T _A = +70°C		0.90	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	89	°C/W
	t < 10s		57	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	18	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	0.4	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	28	45	mΩ	V _{GS} = 4.5V, I _D = 5.0A
		—	36	55		V _{GS} = 2.5V, I _D = 4.2A
Forward Transfer Admittance	Y _{fs}	—	9	—	S	V _{DS} = 5V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.75	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	389	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	72	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	63	—	pF	
Gate Resistance	R _g	—	2.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.7	—	nC	V _{DS} = 15V, I _D = 5.8A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	12	—	nC	
Gate-Source Charge	Q _{gs}	—	0.7	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.5	—	nC	
Turn-On Delay Time	t _{D(on)}	—	5	—	ns	V _{DS} = 10V, V _{GS} = 4.5V, R _G = 6Ω, I _{DS} = 1A
Turn-On Rise Time	t _r	—	8	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	25	—	ns	
Turn-Off Fall Time	t _f	—	8	—	ns	
Reverse Recovery Time	t _{rr}	—	8.5	—	ns	I _F = 5A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{rr}	—	2.1	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

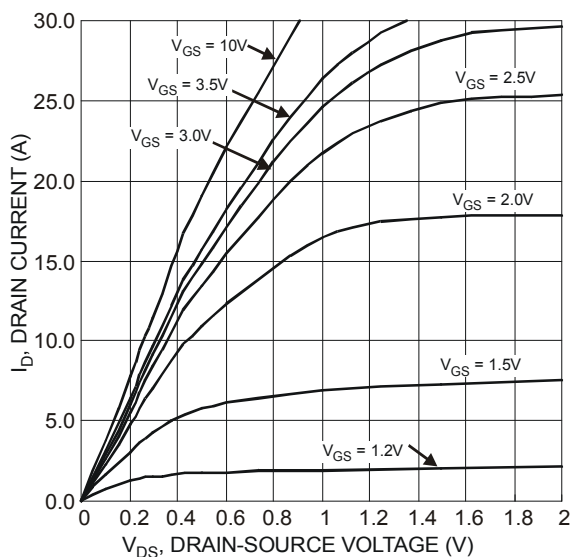


Figure 1 Typical Output Characteristics

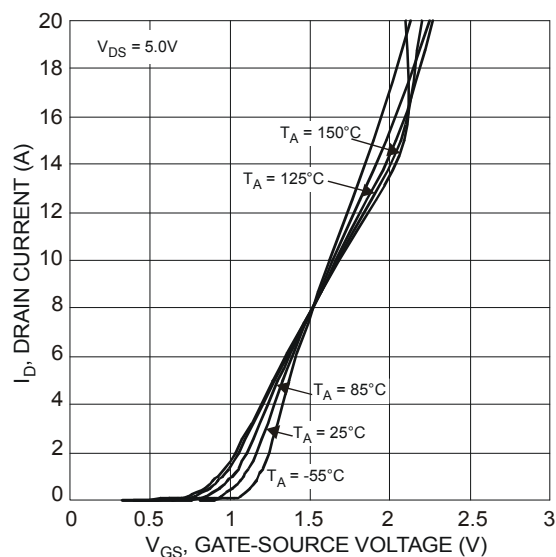


Figure 2 Typical Transfer Characteristics

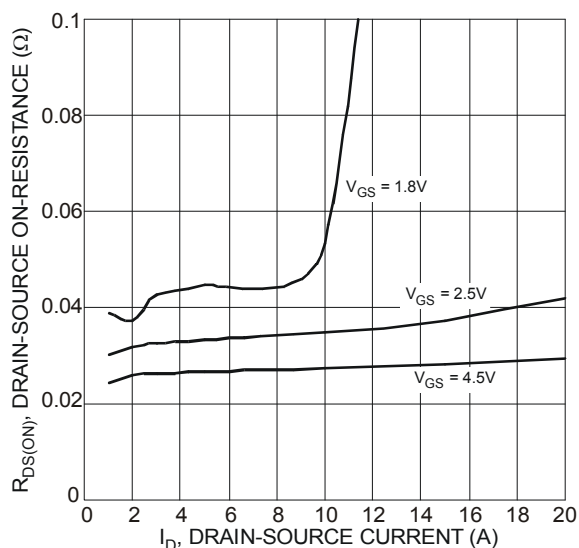


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

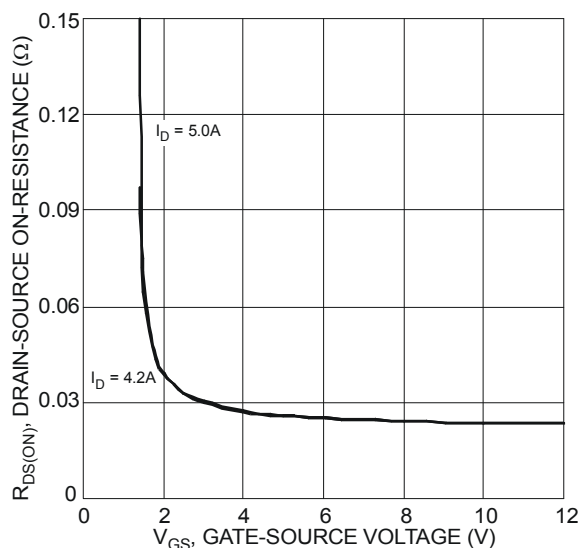


Figure 4 Typical Transfer Characteristics

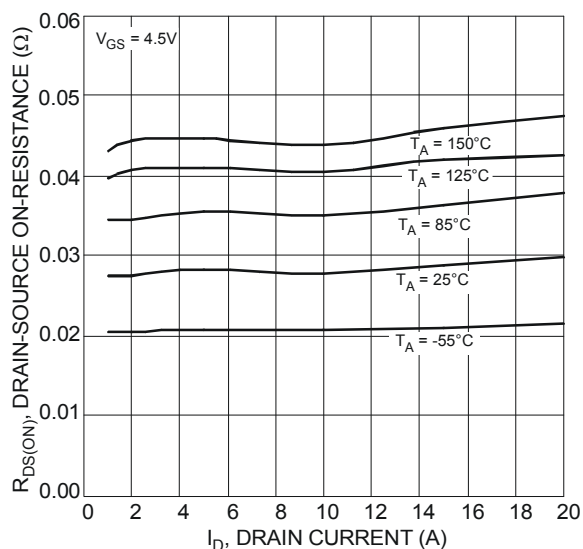


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

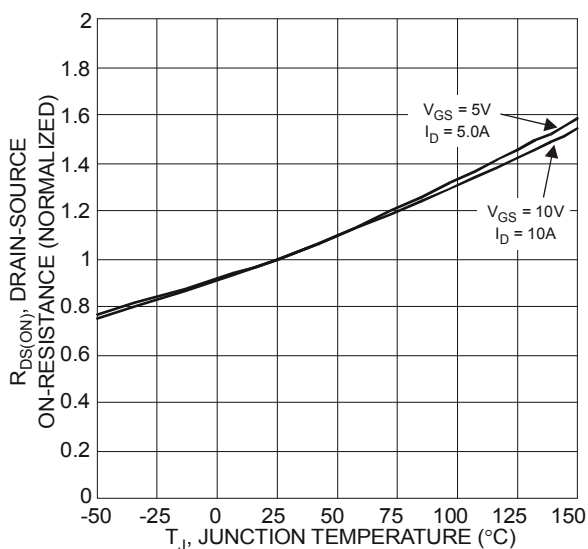
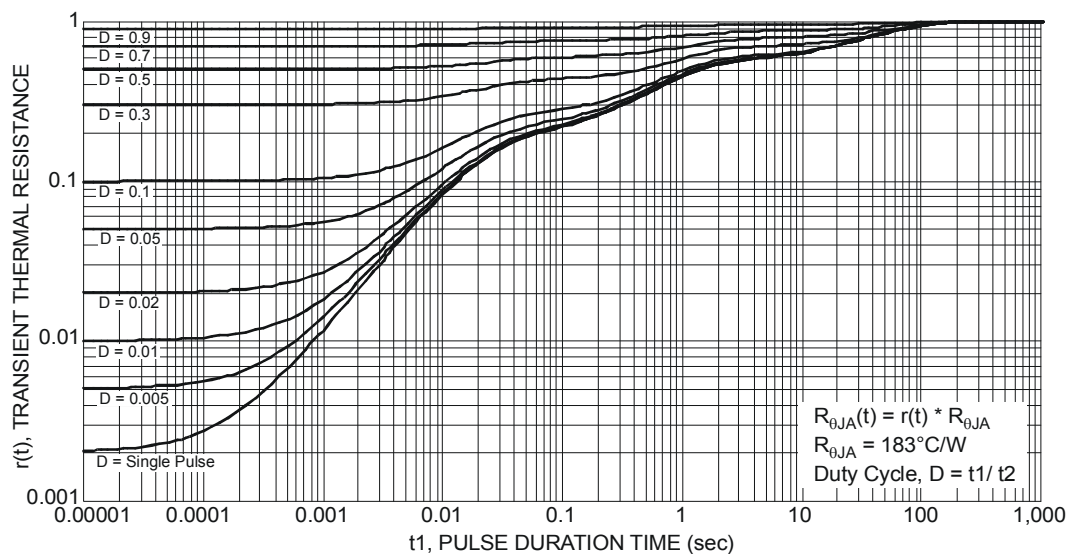
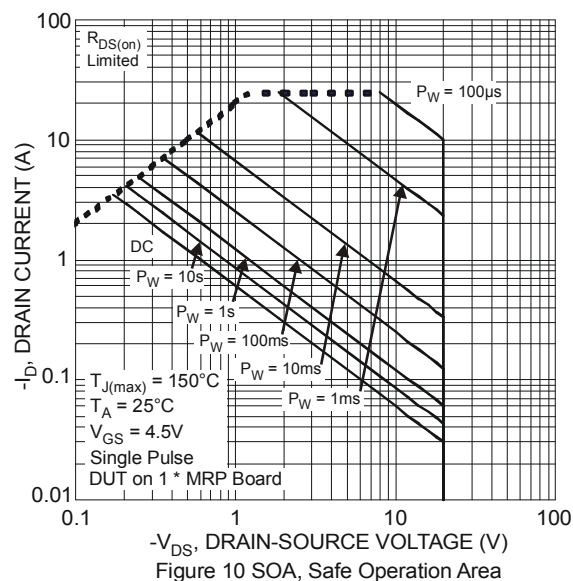
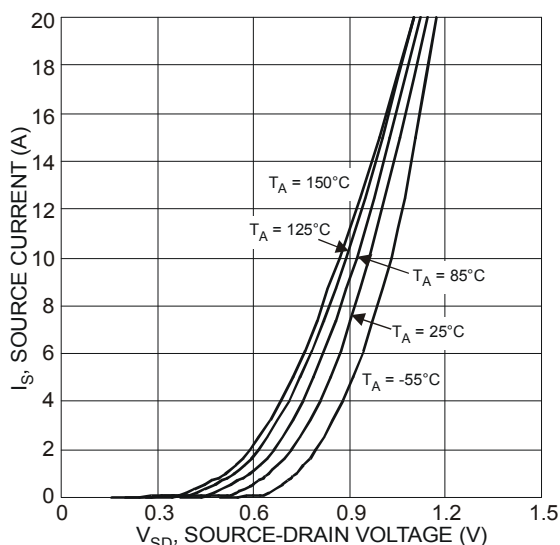
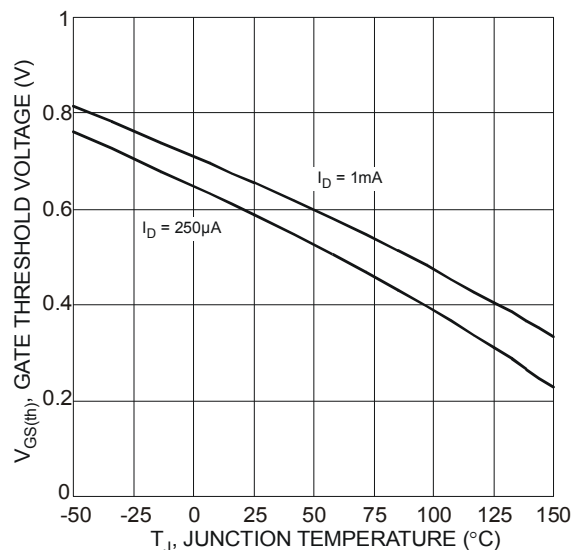
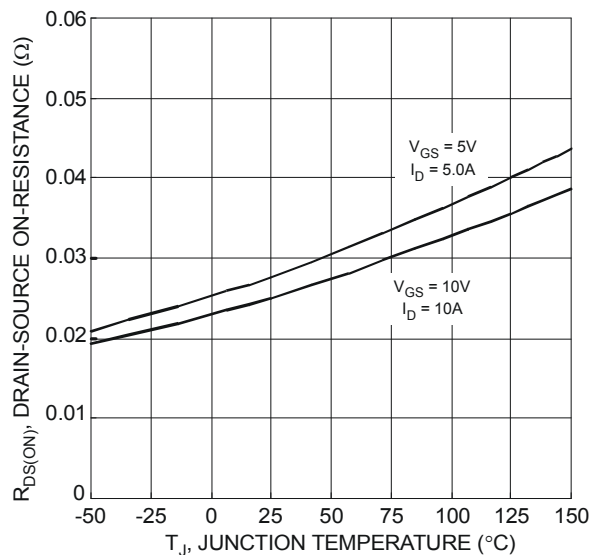
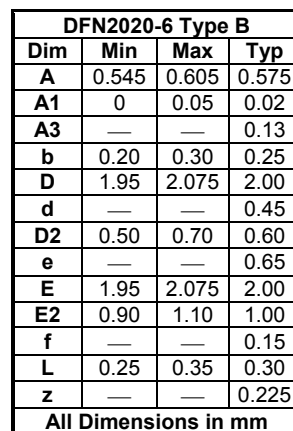


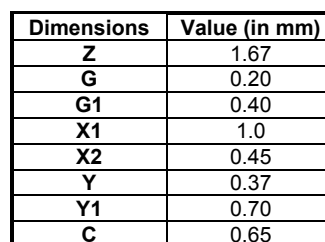
Figure 6 On-Resistance Variation with Temperature



Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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